

# SPP80N03S2L05AKSA1

### SPP80N03S2L05AKSA1 Information



For Reference Only

Part Number SPP80N03S2L05AKSA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 30V 80A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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### SPP80N03S2L05AKSA1 Specifications

Manufacturer Part Number         SPP80N03S2L05AKSA1           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2V @ 110µA           Gate Charge (Qg) (Max) @ Vgs         89.7nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3320pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         167W (Tc)           Rds On (Max) @ Id, Vgs         5.2 mOhm @ 55A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3		
Category         Discrete Semiconductor Products           Package         TO-220-3           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2V @ 110µA           Gate Charge (Qg) (Max) @ Vgs         89.7nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3320pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         167W (Tc)           Rds On (Max) @ Id, Vgs         5.2 mOhm @ 55A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3-1           Package / Case         TO-220-3	Manufacturer Part Number	SPP80N03S2L05AKSA1
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs 89.7nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.2 mOhm @ 55A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Series	OptiMOS?
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Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  5.2 mOhm @ 55A, 10V  Operating Temperature  Supplier Device Package  PG-TO220-3-1  Package / Case  80A (Tc)  80A (T	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Rput Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Standard Temperature  167W (Tc)  Standard Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id       2V @ 110μA         Gate Charge (Qg) (Max) @ Vgs       89.7nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3320pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       167W (Tc)         Rds On (Max) @ Id, Vgs       5.2 mOhm @ 55A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3-1         Package / Case       TO-220-3	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs       89.7nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       3320pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       167W (Tc)         Rds On (Max) @ Id, Vgs       5.2 mOhm @ 55A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3-1         Package / Case       TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  5.2 mOhm @ 55A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs5.2 mOhm @ 55A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3-1  Package / Case  TO-220-3	Power Dissipation (Max)	167W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	5.2 mOhm @ 55A, 10V
Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO220-3-1
Report errors?	Package / Case	TO-220-3
		Report errors?

#### SPP80N03S2L05AKSA1 Guarantees



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### SPP80N03S2L05AKSA1 Payment Methods



















## SPP80N03S2L05AKSA1 Shipping Methods













If you have any question about SPP80N03S2L05AKSA1, please do not hesitate to contact us!

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